

ABSTRACT

There is provided a method for polishing a wafer in which linear defects are not generated. The polishing method comprises the steps of:
5 holding a wafer on a rotatable wafer holding plate; and polishing a surface of the being in contact with a polishing cloth adhered on a rotatable table in such a state that a polishing agent is supplied onto the polishing cloth, wherein the polishing agent is an alkaline solution which contains silica having particles each in the shape of almost an sphere as a main component
10 and further an organic base or a salt thereof. A quaternary ammonium hydroxide is used as the organic base or the salt thereof.